

60V N-Channel Power MOSFET

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. It is suitable for automotive application.

• Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- High GOX reliability
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Load switch

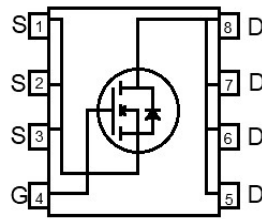
• Ordering Information:

Part NO.	ZMS030N06NY
Marking	ZM030N06
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

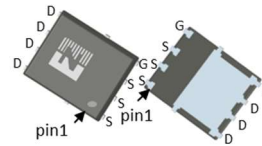
• Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		60	V
Gate-Source Voltage	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	100	A
	I_D	$T_C=75^\circ\text{C}$	83	A
	I_D	$T_C=100^\circ\text{C}$	67	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	400	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	94	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3.8	W
Operating Junction Temperature	T_J		-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +150	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	L=0.1mH, VGS=10V, Rg=25 Ω ,	245	mJ
		L=0.5mH, VGS=10V, Rg=25 Ω ,	515	mJ
ESD Level (HBM)			CLASS 2	

• Product Summary



$V_{DS} = 60\text{V}$
 $R_{DS(ON)} = 2.8\text{m}\Omega$
 $I_D = 100\text{A}$



DFN5 x 6



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	1.6	°C/W
Thermal resistance, junction-ambient ^①	R_{thJA}		-	40	°C/W
Soldering temperature (total time<10s)	T_{sold}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.4	1.7	2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS} = 0V, V_{DS} = 60V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 30A$		2.8	3.5	m Ω
		$V_{GS} = 4.5V, I_D = 20A$		4	4.5	m Ω
Forward Transconductance	g_{FS}	$V_{GS} = 5V, I_{SD} = 10A$		28		S
Diode Forward Voltage	V_{FSD}	$V_{GS} = 0V, I_{SD} = 30A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit	
Input capacitance	C_{iss}	$f = 1MHz, V_{DS} = 25V$	-	4950	-	pF	
Output capacitance	C_{oss}		-	911	-		
Reverse transfer capacitance	C_{rss}		-	33	-		
Gate Resistance	R_g	$f = 1MHz$	-	2.1		Ω	
Total gate charge	Q_g	$V_{DD} = 15V, I_D = 30A, V_{GS} = 10V$	-	67	-	nC	
	$Q_g (4.5v)$		-	17	-		
	Gate - Source charge		Q_{gs}	-	10.8		-
	Gate - Drain charge		Q_{gd}	-	6.8		-
Turn-ON Delay time	$t_{D(on)}$	$V_{GS} = 10V, V_{DS} = 15V, R_G = 3.3\Omega, I_D = 20A$	-	3.6	-	ns	
Turn-ON Rise time	t_r		-	1	-	ns	
Turn-Off Delay time	$t_{D(off)}$		-	20	-	ns	
Turn-Off Fall time	t_f		-	8	-	ns	
Reverse Recovery Time	t_{RR}		$V_{DD} = 20V, di_S/dt = 100A/s, I_S = 20A$	-	40	-	ns
Reverse Recovery Charge	Q_{RR}		-	38	-	nC	

Fig.1 Gate-Charge Characteristics

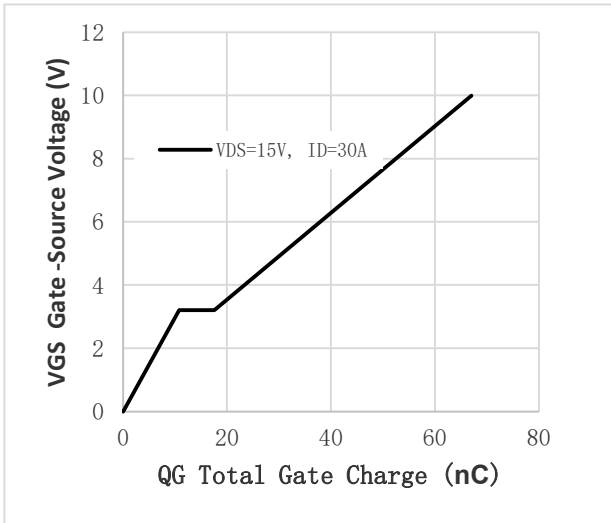


Fig.2 Capacitance Characteristics

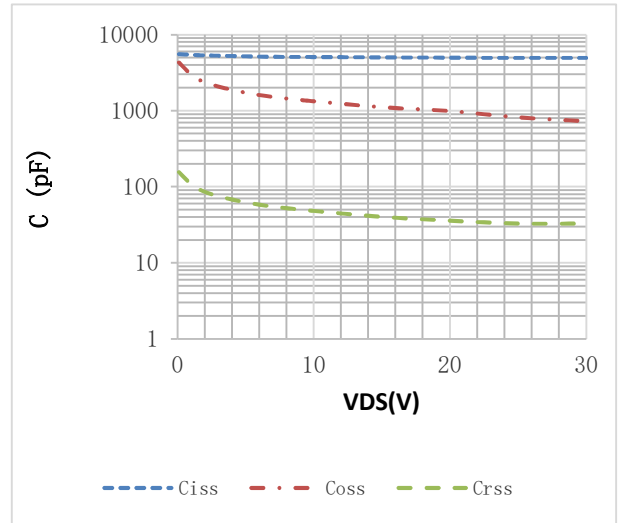


Fig.3 Power Dissipation

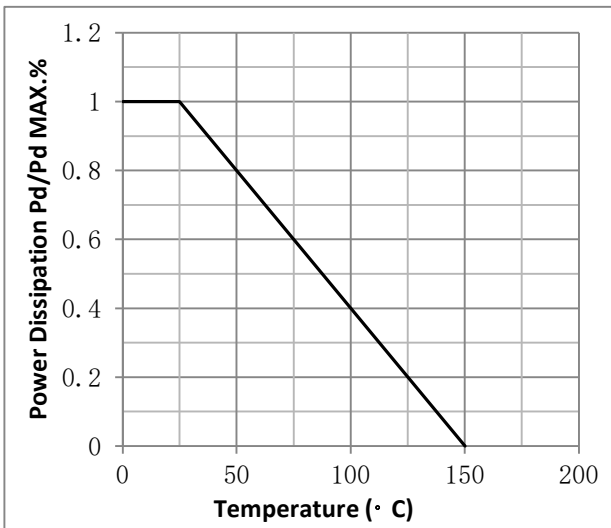


Fig.4 Typical output Characteristics

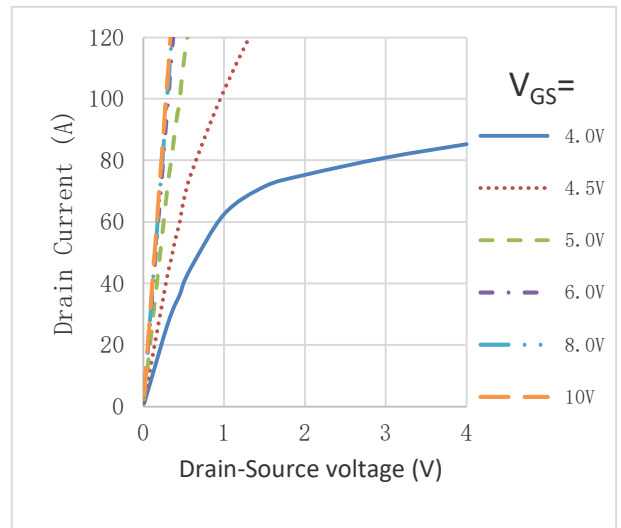


Fig.5 Threshold Voltage V.S Junction Temperature

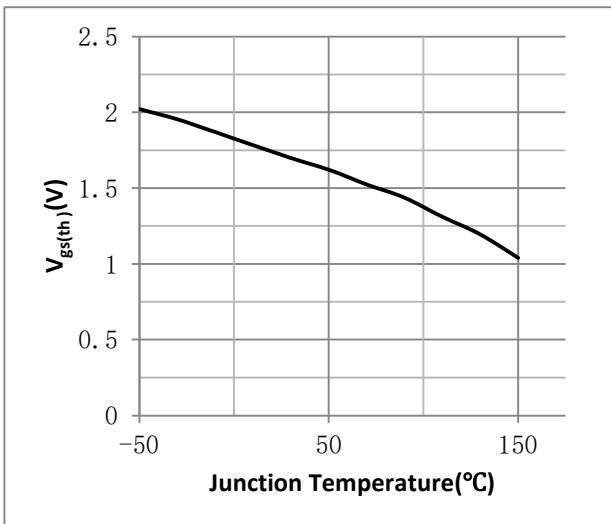


Fig.6 Resistance V.S Drain Current

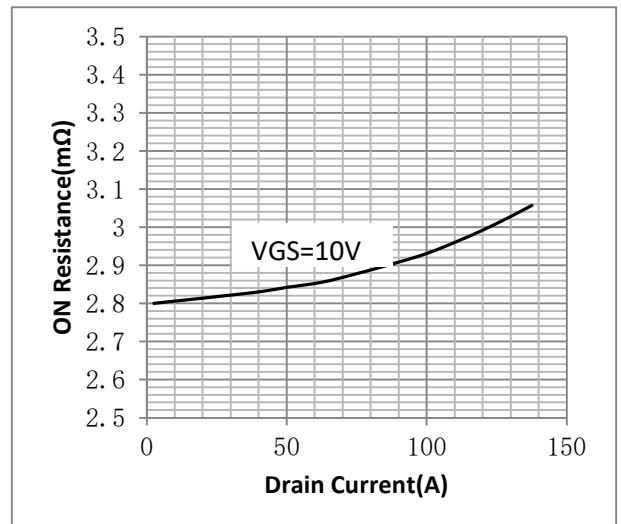


Fig.7 On-Resistance VS Gate Source Voltage

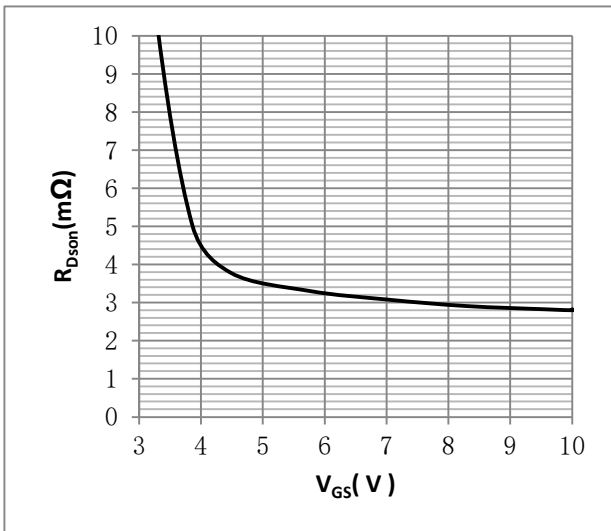


Fig.8 On-Resistance V.S Junction Temperature

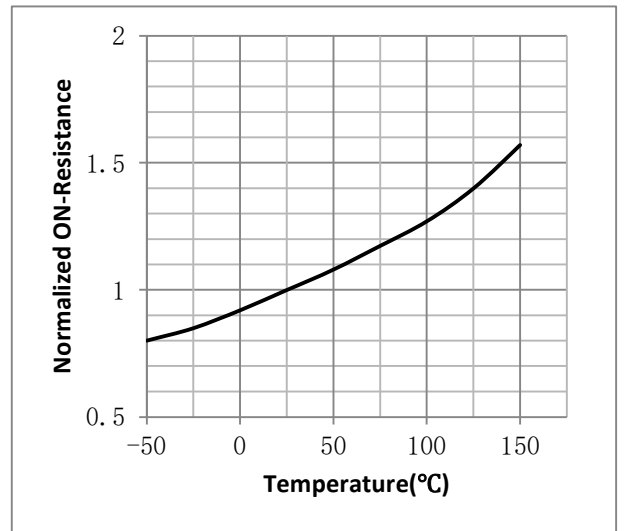


Figure 9. Diode Forward Voltage vs. Current

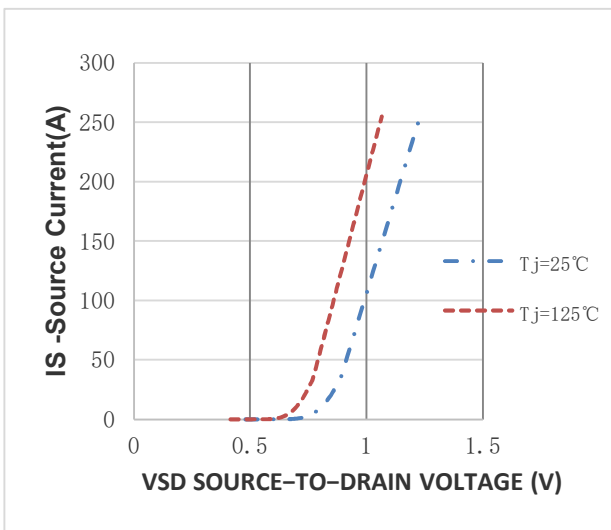


Figure 10. Transfer Characteristics

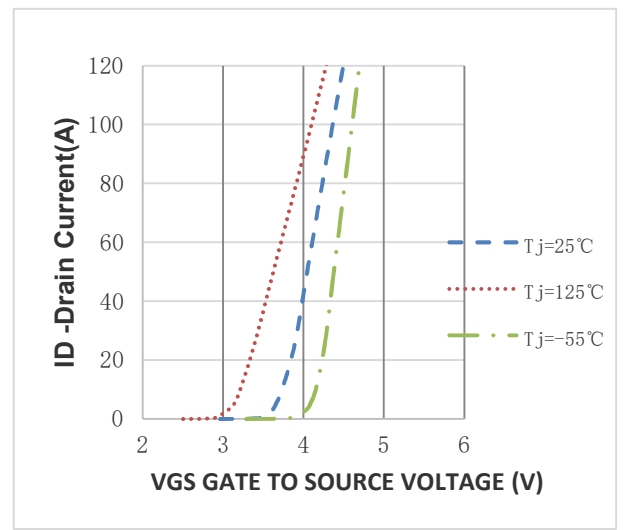


Fig.11 SOA Maximum Safe Operating Area

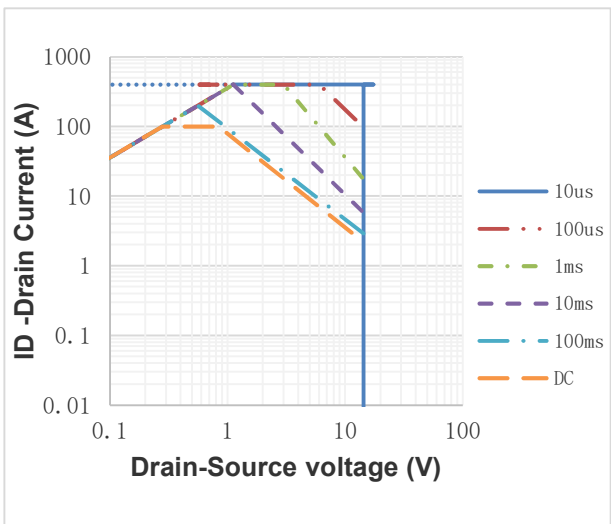
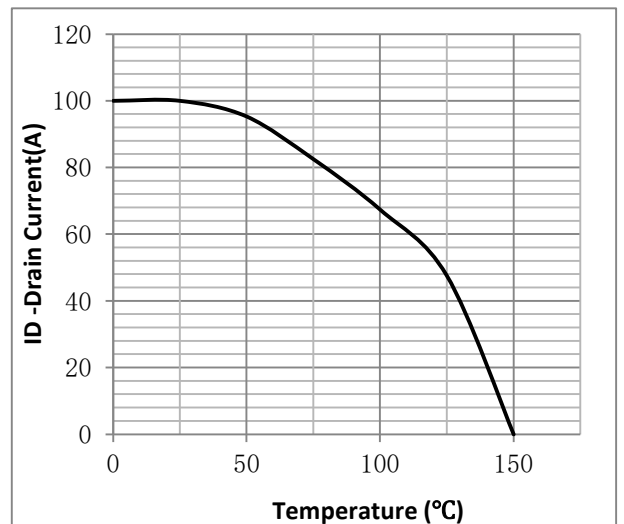
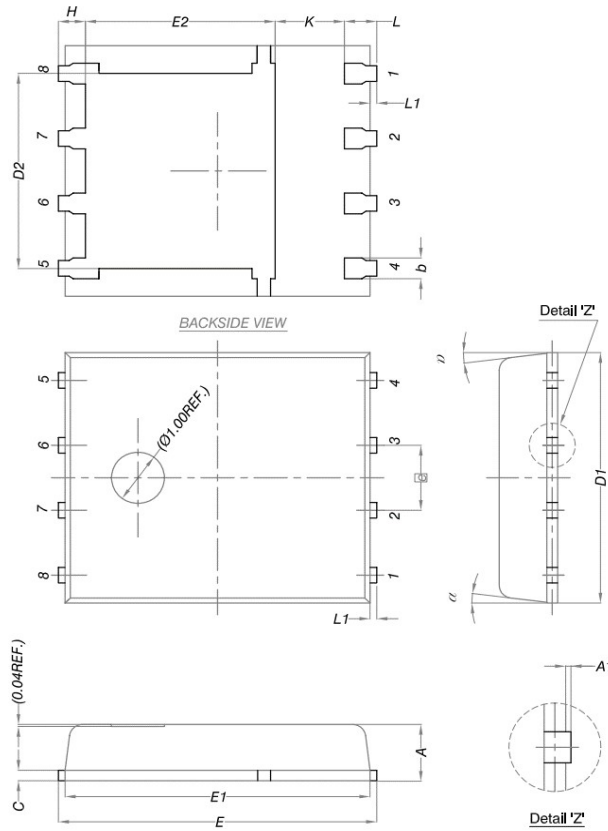


Fig.12 ID vs. Case Temperature^②



•DFN5*6 Package Outline



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°

Note:

- ① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ② Practically the current will be limited by PCB, thermal design and operating temperature. VGS=10V.

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Revision History

Version	Date	Change
A	2023. 9. 10	NEW